

SANYO

No.3103A

2SA1624

PNP Epitaxial Planar Silicon Transistor

Color TV Chroma Output,
High-Voltage Driver Applications**Features**

- High breakdown voltage
- Small reverse transfer capacitance and excellent high frequency characteristics
- Adoption of FBET process

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	-300	V
Collector to Emitter Voltage	V_{CE0}	-300	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-100	mA
Peak Collector Current	i_{cp}	-200	mA
Collector Dissipation	P_C	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

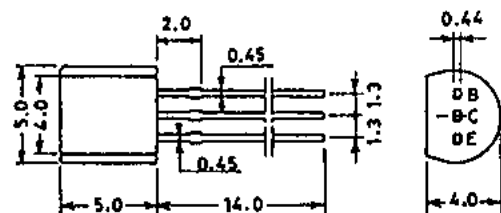
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -200\text{V}, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	60		320	
Gain-Bandwidth Product	f_T	$V_{CB} = -30\text{V}, I_C = -10\text{mA}$		70		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$			-0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -1\text{mA}$			-1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-300			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, R_{BE} = \infty$	-300			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = \infty$	-5			V
Output Capacitance	C_{ob}	$V_{CB} = -30\text{V}, f = 1\text{MHz}$		2.4		pF
Reverse Transfer Capacitance	C_{ro}	$V_{CB} = -30\text{V}, f = 1\text{MHz}$		1.5		pF

※ : The 2SA1624 is classified by 1mA h_{FE} as follows :

60	D	120	100	E	200	160	F	320
----	---	-----	-----	---	-----	-----	---	-----

Case Outline 2003A
(unit : mm)



JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

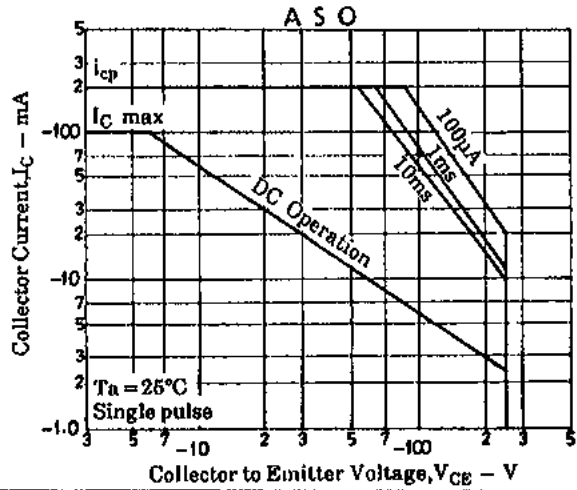
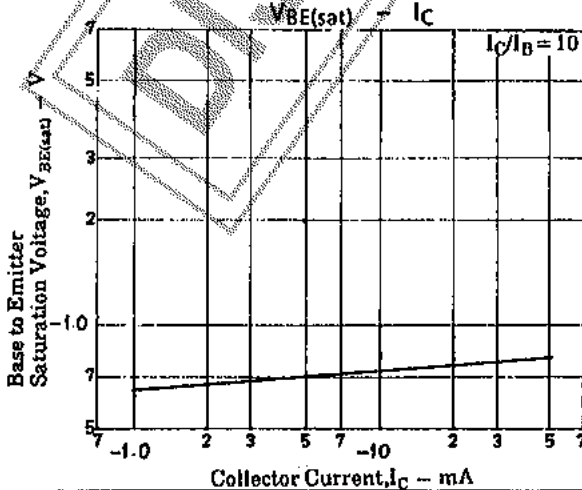
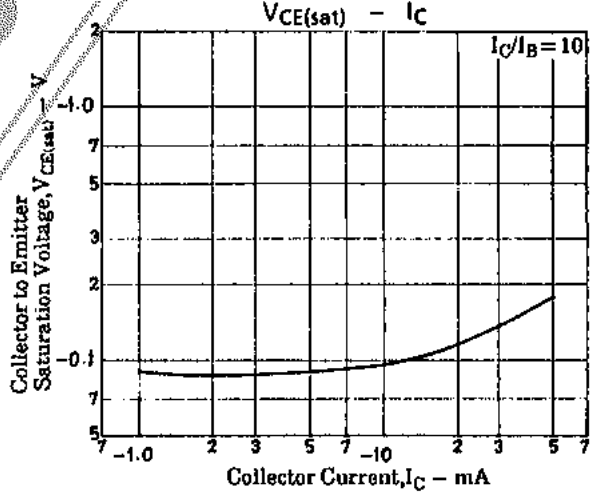
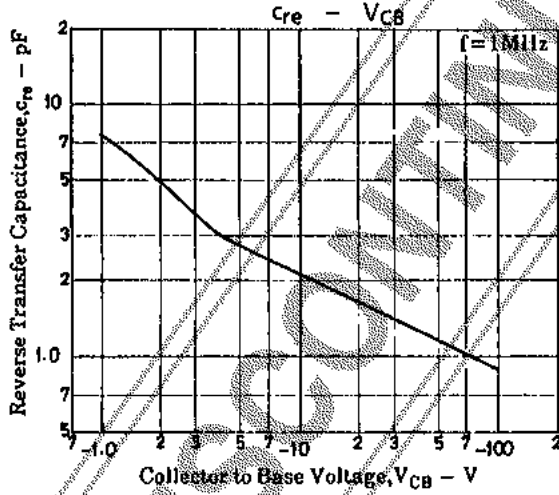
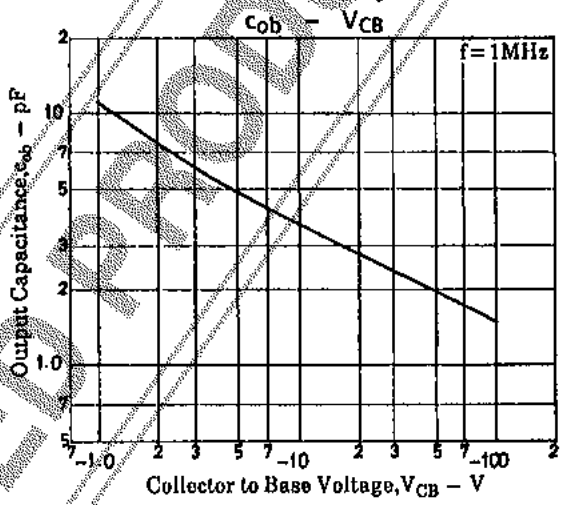
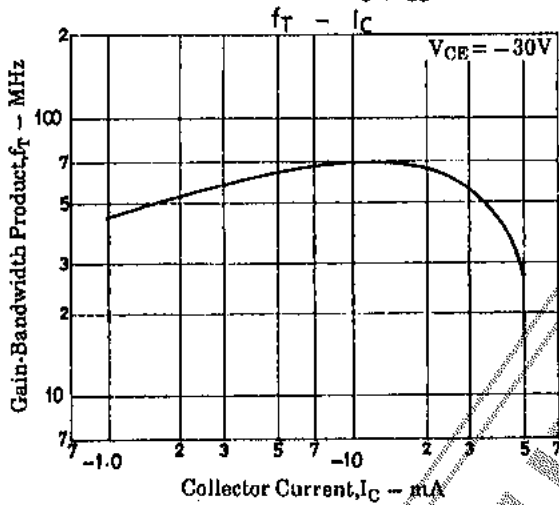
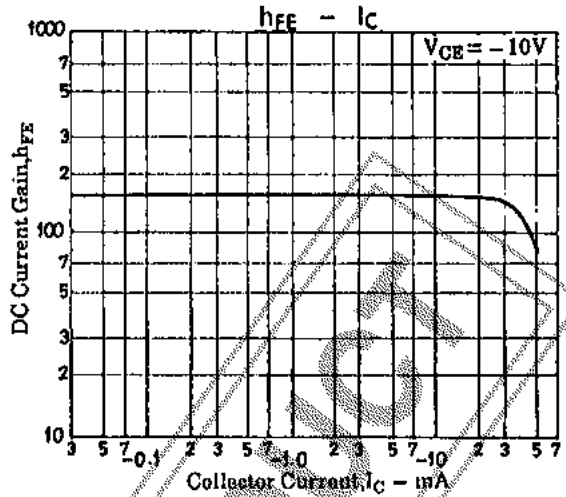
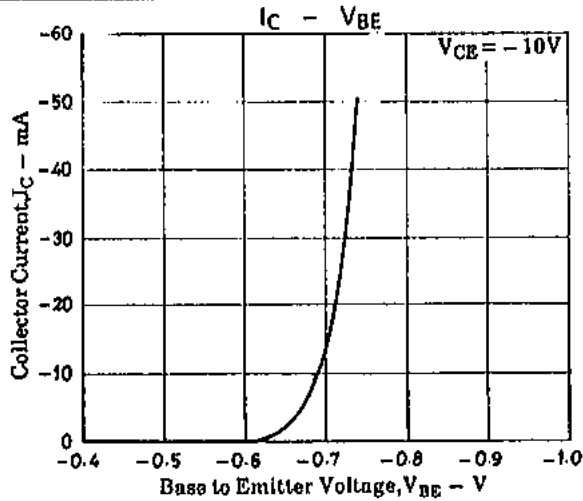
B: Base
C: Collector
E: Emitter

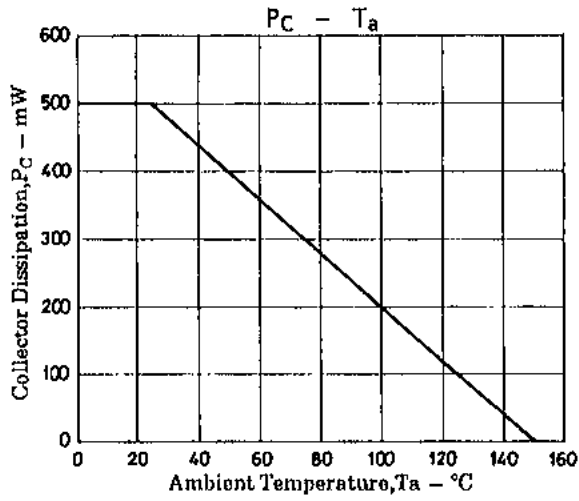
Specifications and information herein are subject to change without notice.

SANYO Electric Co., Ltd. Semiconductor Overseas Marketing Div.
Natsume Bldg., 18-6, 2-chome, Yushima, Bunkyo-ku, TOKYO 113 JAPAN

5070MO/N149MO,TS No.3103-1/3

2SA1624





The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.

DISCONTINUED PRODUCT